



PMS-01-1440C

May 11, 2004

To: Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/822,197 04/09/04

Kuo-Chi Tu et al.

METHOD OF FABRICATING AN EMBEDDED  
DRAM FOR METAL-INSULATOR-METAL  
(MIM) CAPACITOR STRUCTURE

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.


The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on May 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 5/17/04

TSMC-01-1440C

U.S. Patent 6,211,061 to Chen et al., "Dual Damascene Process for Carbon-Based Low-K Materials," teaches a dual damascene process with carbon-based low-k materials.

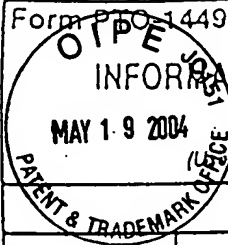
The following three U.S. Patents discuss MIM capacitor processes:

- 1) U.S. Patent 6,096,597 to Tsue et al., "Method for Fabricating an Integrated Circuit Structure."
- 2) U.S. Patent 6,329,234 to Ma et al., "Copper Process Compatible CMOS Metal-Insulator-Metal Capacitor Structure and Its Process Flow."
- 3) U.S. Patent 6,271,084 to Tu et al., "Method of Fabricating a Metal-Insulator-Metal (MIM) Capacitor Structure Using a Damascene Process."

Sincerely,

A handwritten signature in black ink, appearing to read "SBA", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,  
Reg. No. 37761



# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

MAY 19 2004

(Use several sheets if necessary)

Document Number (Optional)

TSMC-01-1440C

Application Number

10/822,197

Applicant

Kuo-Chi Tu et al.

Filing Date

04/09/04

Group Art Unit

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
	6211061	4/3/01	Chen et al.	438	622	10/29/99
	6096597	8/1/00	Tsu et al.	438	240	1/28/98
	6329234	12/11/01	Ma et al.	438	210	7/24/00
	6271084	8/7/01	Tu et al.	438	253	1/16/01

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.